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Descargar 5 Edition de Fundamentos De QuimicaIn the microelectronics industry, interconnection of microelectronic devices is continuously pursued with a view towards both size reduction and an increase in the number of transistors per unit area of the microelectronic substrate. One particular approach to size reduction and increased transistor density is to reduce the feature size of the microelectronic device to the submicron range. However, the limitations of photolithography have thwarted much of this trend. In order to achieve further size reduction and increased transistor density, one possible strategy has been to replace photolithography with a suitable alternative such as, for example, scanning probe lithography, electron beam lithography, nanoimprint lithography, or nanoimprint lithography. A nanoimprint lithography tool comprises a substrate having a mold formed thereon, an imprinting device, and a method of operation for the device. The imprinting device is provided with a form defining a surface of the mold with a relief pattern, the imprinting device is operated on a surface of the substrate, a substrate having a thin film formed thereon is inserted into the imprinting device, the imprinting device is removed and the thin film is imprinted. The substrate, which may be a semiconductor substrate, is mounted on a chuck of a positioning device. Thereafter, the imprinting device is brought into contact with the chuck, the chuck is rotated, and the imprinting device is moved in an x, y, and z direction above the chuck. The imprinting device then releases the thin film which has been transferred to the surface of the substrate. The positioning device then removes the imprinting device from the substrate, a thin film is formed on a material of the substrate, and the material is subjected to processing such as, for example, etching to remove the mold. However, conventional nanoimprint lithography devices are disadvantageous in that, in operation, the imprinting device is used to directly imprint a mold on the substrate which, in some cases, may be a fragile material. For example, the substrate may be a semiconductor wafer which may be relatively fragile and may be easily damaged. Thus, the imprinting device may cause premature damage to the semiconductor wafer which may result in a significant reduction in the yield of operation of the device. It is therefore desirable to provide a device and method for producing a molded thin film on a substrate which overcomes the disadvantages of the prior art.Q: 3e33713323